ECE 536 – Integrated Optics and Optoelectronics Lecture 23 – April 13, 2022

Spring 2022

Tu-Th 11:00am-12:20pm Prof. Umberto Ravaioli ECE Department, University of Illinois

Lecture 23 Outline

- Distributed Bragg Reflector Lasers
 - Vertical Cavity Surface Emitting (VCSEL) Laser
 - In plane edge emitting DBR Laser

Applications of gratings in lasers – Distributed Feedback (DFB) Laser



Distributed Feedback (DFB) Laser



DFB Lasers provide tight control of channel wavelength and minimize chromatic dispersion (important in systems for long distance optical communications)

The reflection coefficient depends on

- *K* Coupling coefficient
- δ Detuning parameter

 $egin{aligned} eta_B &= \ell \, \pi / \Lambda & ext{Bragg wave number} \ \ell & ext{Order of grating (integer)} \end{aligned}$

Transmission Characteristic for DFB



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DBF Structure with End Facets



The transmission matrix method can be applied to relate A_t with A(O)

Effect of Cavity End Conditions: Facet Coating Symmetrical Cavity



Effect of Cavity End Conditions: Facet Coating Asymmetrical Cavity



Lasing Peak can be obtained to operate on either side of stopband



Phase Shifted DFB breaks the degeneracy



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Phase Shifted DFB breaks the degeneracy



 $\lambda/4$ -Phase-shift grating

Intuitive Picture



FIGURE 2.6. Schematic representation of longitudinal modes in DFB lasers with a uniform grating and $\lambda/4$ -shifted DFB lasers. Corrugations and standing waves around the center of the laser axis are shown at the left-hand side of the figure.

[N. Chinone and M. Okai, "Distributed Feedback Semiconductor Lasers" Chapter 2 in *Semiconductor Lasers: Past, Present, and Future,* G.P. Agrawal, editor (1995)]

Applications of gratings in lasers – Distributed Bragg Reflector (DBR) laser

Vertical Cavity Surface Emitting (VCSEL) lasers



Applications of gratings in lasers – Distributed Bragg Reflector (DBR) laser

Edge emitting lasers



VCSEL

Basic VCSEL Structure





$$g_{th} = \alpha_i + \alpha_m$$

$$g(n) = g'(n - n_{tr})$$

$$\begin{cases} g_{th} = \frac{(\alpha_i + \alpha_m)}{\Gamma} \\ n_{th} = n_{tr} + \frac{(\alpha_i + \alpha_m)}{\Gamma g'} \\ J_{th} = \frac{qd}{\eta_i} \frac{n_{th}}{\tau_e(n_{th})} \end{cases}$$

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 $n_1 = 3.6$

 $n_2 = 3.4$

 $\Gamma \approx 0.28$

confinement factor

$$\Gamma = \frac{\frac{+d/2}{\int} |U|^2 dx}{\int \frac{-d/2}{+\infty} |U|^2 dx}$$

good approximation

 $\Gamma \cong D^2/(2+D^2)$

$$D = 2\pi (n_1^2 - n_2^2)^{1/2} d/\lambda$$

normalized thickness of active layer





confinement factor

$$\Gamma = \frac{\frac{+d/2}{\int} |U|^2 dx}{\int \frac{-d/2}{+\infty} |U|^2 dx}$$

QW – Approximate with

$$U \propto \exp[-x^2/w_{spot}^2]$$

 $d_{SCH} = 2w_{spot}$
 $\Gamma \approx \frac{d}{0.62 d_{SCH}}$

QW Laser – Example $d_{SCH} = 1.0 \ \mu \text{m}$ $d = 10 \ \text{nm}$ $\Gamma \approx 1.6 \times 10^{-2}$



QW Laser – Example

 $d_{SCH} = 1.0 \ \mu m$ $d = 10 \ nm$ $\Gamma = 1.6 \times 10^{-2}$ $L = 300 \ \mu m$ $\alpha_i = 10 \ cm^{-1}$ R = 0.32 $g' = 6 \times 10^{-16} \ cm^2$ $N_{tr} = 2 \times 10^{18} \ cm^{-3}$ $\eta_i \approx 1$ $\tau_e = 4 \ ns$

$$d_{SCH}$$
QW Laser - Example
$$d_{SCH} = 1.0 \ \mu\text{m}$$

$$d = 10 \ \text{nm}$$

$$\Gamma = 1.6 \times 10^{-2}$$

$$L = 300 \ \mu\text{m}$$

$$\alpha_i = 10 \ \text{cm}^{-1}$$

$$R = 0.32$$

$$g' = 6 \times 10^{-16} \ \text{cm}^2$$

$$N_{tr} = 2 \times 10^{18} \ \text{cm}^{-3}$$

$$\eta_i \approx 1$$

$$\tau_e = 4 \ \text{ns}$$

$$\gamma = \alpha_i L + \ln(1/R) = 1.4394$$

$$N_{th} = \frac{\gamma}{\Gamma g' L} + N_{tr} = 5 \times 10^{18} + 2 \times 10^{18} \ \text{cm}^{-3}$$

$$J_{th} = \left(\frac{q \ d}{\eta_i \ \tau_e}\right) N_{th} = 4 \times 10^{-17} \times 7 \times 10^{18} \ \text{cm}^{-3}$$

$$= 280 \ \text{A/cm}^2$$

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$$= 280 \text{ A/cm}^2$$



- Reduces transparency density
- Increase differential gain

VCSEL

It is not straightforward to formulate a simple model for threshold



Very short cavity L = Small gain somewhat compensated by high reflectivity mirrors VCSEL



Simple picture

volume occupied by active carriers

cavity volume occupied by photons

$$\frac{V_{\rm w}}{V_{\rm p}} = \Gamma = \Gamma_z \cdot \Gamma_{\rm t} = \frac{d_{\rm a}}{L_{\rm eff}} \cdot \Gamma_{\rm t}$$

where $0 < \Gamma_{
m t} \leq 1$ and often $\Gamma_{
m t} pprox 1$

The Modern VCSEL



VCSEL



Some authors use L_{eff} for the total length of the cavity as above.

Coldren, Corzine and Mašanović use the same to indicate the effective length at which to place a mirror that gives the same reflection coefficient as the grating as in the diagram below



FIGURE 3.15: Definition of an effective mirror for a grating reflector. ²⁶

VCSEL - Resonance condition



VCSEL – Relative Confinement factor or Gain Enhancement factor

$$\Gamma_{\rm r} = \frac{L}{d_{\rm a}} \, \frac{\int_{d_{\rm a}} |E(z)|^2 \, \mathrm{d}z}{\int_L |E(z)|^2 \, \mathrm{d}z}$$

Approximate field in the central part of the cavity (z = 0 at center of cavity)

$$E(z) = E_0 \cos\left(2\pi \langle \bar{n} \rangle z / \lambda\right)$$

for an optimally positioned active region one can show that

$$\Gamma_{\rm r} = 1 + \frac{\sin(2\pi \langle \bar{n} \rangle d_{\rm a}/\lambda)}{2\pi \langle \bar{n} \rangle d_{\rm a}/\lambda} \ge \mathbf{1}$$

For the 3 QW system shown earlier, $\Gamma_{
m r}=1.8$ For a single thin QW, $\Gamma_{
m r} o 2$ For $d_{
m a}=m\lambda/(2\langlear{n}
angle)$ we have $\Gamma_{
m r}=1$

VCSEL – Threshold Gain and Photon Lifetime

$$g_{\rm th} = \alpha_{\rm a} + \frac{1}{\Gamma_{\rm r} d_{\rm a}} \left[\alpha_{\rm i} (L_{\rm eff} - d_{\rm a}) + \ln \frac{1}{\sqrt{R_{\rm t} R_{\rm b}}} \right]$$

losses in active region

OK for lossless mirrors (but gratings are usually lossy)

$$\frac{1}{\tau_{\rm p}} = \frac{d_{\rm a}}{L_{\rm eff}} \langle v_{\rm gr} \rangle \Gamma_{\rm r} g_{\rm th} \approx \langle v_{\rm gr} \rangle \left[\alpha_{\rm i} + \frac{1}{L_{\rm eff}} \ln \frac{1}{\sqrt{R_{\rm t} R_{\rm b}}} \right]$$
$$\boxed{\langle v_{\rm gr} \rangle = c / \langle \bar{n}_{\rm gr} \rangle}$$

Example

 $d_a = 24 \text{ nm} \qquad \Gamma_r = 1.8$ $L_{eff} = 1.3 \text{ } \mu\text{m} \qquad \alpha_a \ll g_{th}$ $R_t = R_b = 0.995 \qquad \langle \bar{n}_{gr} \rangle = 3.6$ $\alpha_i = 10 \text{ } \text{cm}^{-1}$

$$g_{th} = 1,460 \text{ cm}^{-1}$$

$$\tau_p = 2.5 \text{ ps}$$

VCSEL – Laser Threshold



For the design of high performance VCSELs it is important to know the electric field distribution in the resonator. Assuming linearly polarized waves in a 1-D scalar approach, we have to solve the Helmholtz equation

$$\frac{\mathrm{d}^2 E(z)}{\mathrm{d}z^2} + \gamma^2 E(z) = 0$$

for the phasor of the transverse electric field component $E = E_x$

In each homogeneous *m*th layer

$$\gamma_m = \beta_m - \mathrm{i} \alpha_m / 2$$

 $\beta_m = 2\pi \bar{n}_m / \lambda$

The absorption coefficient fulfills $lpha_m \geq 0$ except from the QW layers, where gain leads to $lpha_m < 0$.

In each layer, the electric field is the superposition of two monochromatic plane waves counterpropagating in the *z*-direction

$$E_m(z) = E_m^+ \exp\{-i\gamma_m(z - z_m)\} + E_m^- \exp\{+i\gamma_m(z - z_m)\}$$

 E_m^+ and E_m^- denote the complex field amplitudes of the waves at the interface



The continuity conditions for the transverse components of electric and magnetic fields lead to relations, between amplitudes in subsequent layers

$$E_m^+ = (\gamma_m^+ E_{m+1}^+ + \gamma_m^- E_{m+1}^-) \exp\{i\gamma_m (z_{m+1} - z_m)\},\$$

$$E_m^- = (\gamma_m^- E_{m+1}^+ + \gamma_m^+ E_{m+1}^-) \exp\{-i\gamma_m (z_{m+1} - z_m)\}\$$

where we have the abbreviations

$$\gamma_m^+ = \frac{\gamma_m + \gamma_{m+1}}{2\gamma_m}$$
 and $\gamma_m^- = \frac{\gamma_m - \gamma_{m+1}}{2\gamma_m}$

Self-oscillation of the layer structure exclusively allows **outgoing** waves in the terminating sections

$$m = 0$$
 $E_0^+ = 0$
 $m = M + 1$ $E_{M+1}^- = 0$

24.5 pairs 18 pairs Norm. electric field amplitude GaAs-AlGaAs GaAs-AlAs top Bragg reflector bottom Bragg reflector λ-cavity 0.5 1.7 µm mm 3 Longitudinal coordinate (µm)

due to the high reflectivities of the mirrors, a pronounced resonant enhancement of the field amplitude is built up

Poynting vector

$$S = \operatorname{Re} \{ E \times H^* \}$$

In the 1-D scalar approach the magnetic field is

$$H = H_y = \frac{\mathrm{i}}{\omega\mu_0} \,\frac{\mathrm{d}E}{\mathrm{d}z}$$

The energy flux in section m of the multilayer structure can be expressed as

$$S_m(z) = \frac{\beta_m}{\omega\mu_0} |E_m^+|^2 \exp\{-\alpha_m(z-z_m)\} - \frac{\beta_m}{\omega\mu_0} |E_m^-|^2 \exp\{\alpha_m(z-z_m)\} + \frac{\alpha_m}{\omega\mu_0} \operatorname{Im}\left\{E_m^+(E_m^-)^* \exp\{-i2\beta_m(z-z_m)\}\right\}.$$

Above threshold current I_{th} , top and bottom light output powers P_t and P_t linearly increase with driving current I. We can write

$$P_{\rm t,b} = \tilde{\eta}_{\rm dt,b} \frac{\hbar\omega}{q} \left(I - I_{\rm th}\right)$$

$$\tilde{\eta}_{\rm dt,b} = \eta_{\rm dt,b} \, \eta_{\rm i}$$

where the differential quantum efficiency

 $\eta_{
m dt,b}$

characterizes the percentage of generated coherent light that is available as top or bottom emission. In well designed VCSELs with high quality active QWs

$$\eta_{i} > 90\%$$

Due to absorption in the mirrors we always find $\eta_{
m dt} + \eta_{
m db} < 100\,\%$

The differential quantum efficiency is identified as the fraction of the generated flux that is emitted through top or bottom mirrors

 $\eta_{\rm d} = \eta_{\rm dt} + \eta_{\rm db}$

$$\eta_{\rm d} = \frac{g_{\rm th}}{g_{\rm th} + \alpha_{\rm a}} \left(1 + \frac{\sum_{i, {\rm pass.}} \Delta S_i}{\sum_{i, {\rm act.}} \Delta S_i} \right) \quad \text{with} \quad \Delta S_i = S(z_{i+1}) - S(z_i)$$

Absorption leads to flux increments

$$\Delta S_i < 0 \qquad \qquad \eta_{\rm d} < 1$$

Denoting top and bottom emitted energy fluxes

$$S_{\rm t} = S(z_1) < 0$$
 and $S_{\rm b} = S(z_{M+1}) > 0$

the corresponding differential quantum efficiencies are

$$\eta_{\rm dt} = \eta_{\rm d} \, \frac{|S_{\rm t}|}{|S_{\rm t}| + |S_{\rm b}|} \qquad \text{and} \qquad \eta_{\rm db} = \eta_{\rm d} \, \frac{|S_{\rm b}|}{|S_{\rm t}| + |S_{\rm b}|}$$
³⁷

Normalized energy flux density



The Modern VCSEL



VCSEL emission characteristics

The active diameter of the VCSEL can be made quite small (few micron size) to reach the lowest possible threshold current (down to sub-100 μ A) but it can also exceed 100 μ m to get power beyond 100mW.

Rule of Thumb: Up to active region diameters of about 4 μ m the VCSEL emits in the single fundamental transverse mode. Larger devices start lasing on several higher order radial and azimuthal modes.

Due to the small length of the laser cavity (1 to 2 µm) consecutive longitudinal modes are widely spaced in wavelength ($\Delta\lambda \approx 100 \text{ nm}$).

If one mode is made to coincide with the peak reflectivity of the mirrors, the two adjacent modes fall outside the high-reflectivity band and single longitudinal mode oscillation can also be established.

VCSEL emission characteristics





Reading Assignments:

- Section 8.5 of Chuang's book
- Sections 11.1 and 11.2 of Chuang's book
- Chapter 3 and Appendix 5 in Coldren, Corzine and Mašanović
- Section 8.2 in Coldren, Corzine and Mašanović